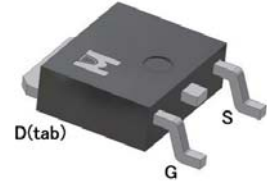
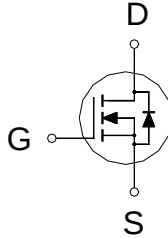




N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	100V
$R_{DS(on)} (MAX.)$	125m Ω
I_D	14A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	14	A
	$T_C = 100^\circ\text{C}$		9.5	
Pulsed Drain Current ¹		I_{DM}	40	
Avalanche Current		I_{AS}	10	mJ
Avalanche Energy	$L = 0.1\text{mH}$, $I_D = 10\text{A}$, $R_G = 25\Omega$	E_{AS}	5	
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	2.5	
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	41	W
	$T_C = 100^\circ\text{C}$		20	
Operating Junction & Storage Temperature Range		$T_{j, T_{stg}}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		3.0	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		52.5	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.8	3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
		$V_{DS} = 70V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	14			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 8A$		105	125	m Ω
		$V_{GS} = 4.5V, I_D = 5A$		120	160	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 8A$		8		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		820		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			43		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		2.5		Ω
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 80V, V_{GS} = 10V,$ $I_D = 8A$		18.7		nC
Gate-Source Charge ^{1,2}	Q_{gs}			3.9		
Gate-Drain Charge ^{1,2}	Q_{gd}			4.8		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 50V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		10		nS
Rise Time ^{1,2}	t_r			7		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			18		
Fall Time ^{1,2}	t_f			12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				14	A
Pulsed Current ³	I _{SM}				40	
Forward Voltage ¹	V _{SD}	I _F = 1A, V _{GS} = 0V			1.0	V
Reverse Recovery Time	t _{rr}	I _F = 5A, dI _F /dt = 100A / μ S		40		nS
Reverse Recovery Charge	Q _{rr}			70		nC

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

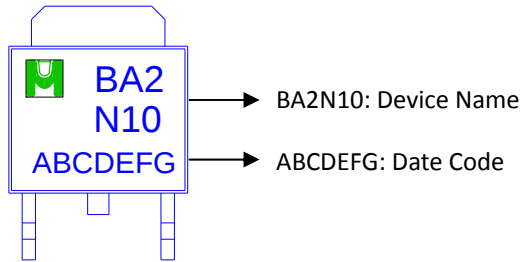
²Independent of operating temperature.



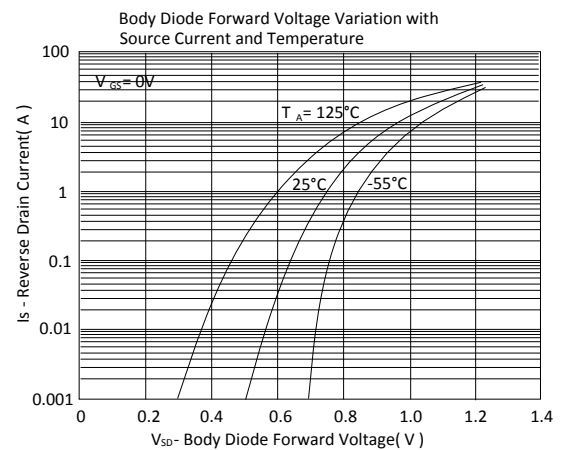
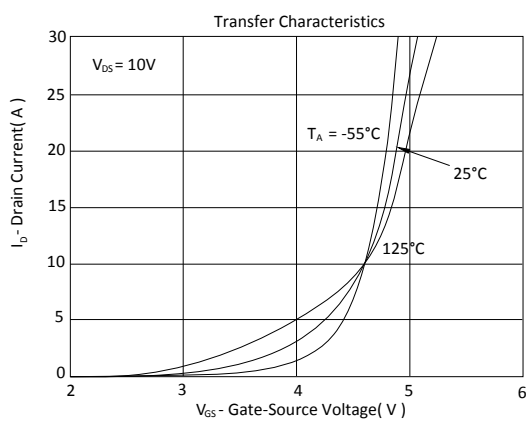
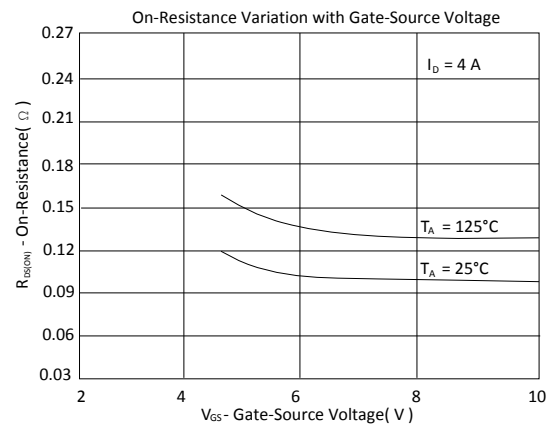
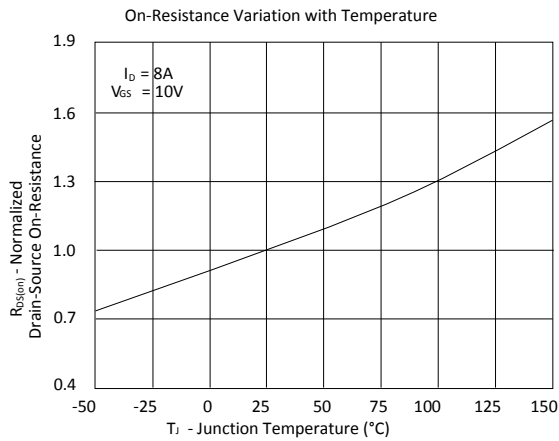
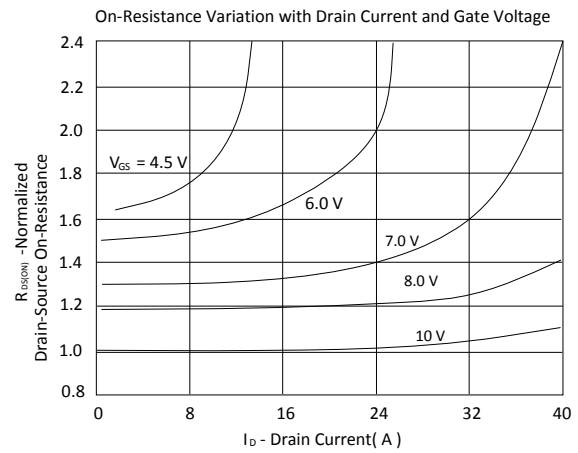
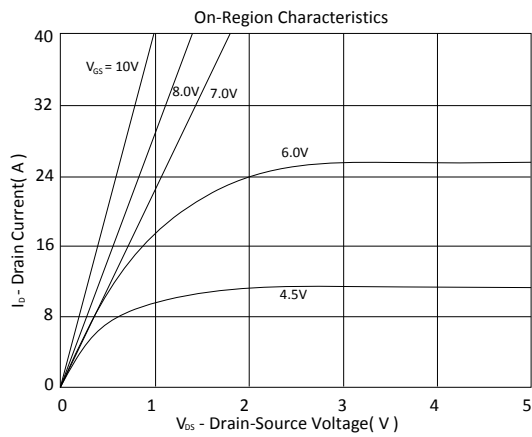
³Pulse width limited by maximum junction temperature.

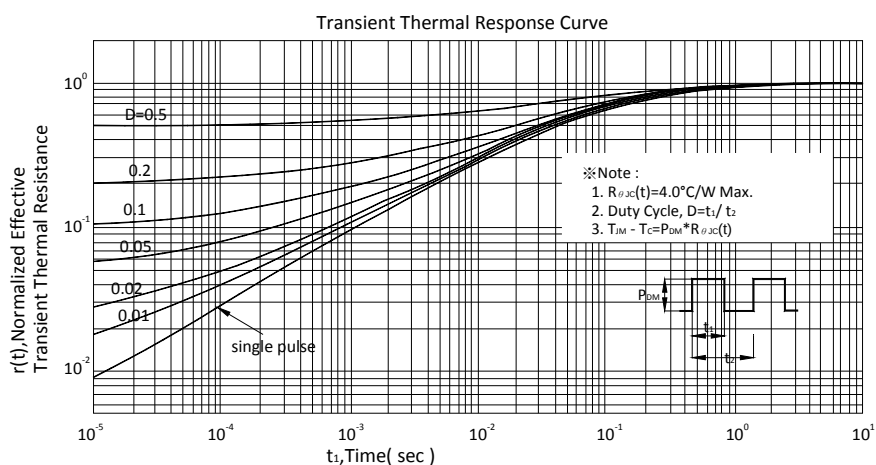
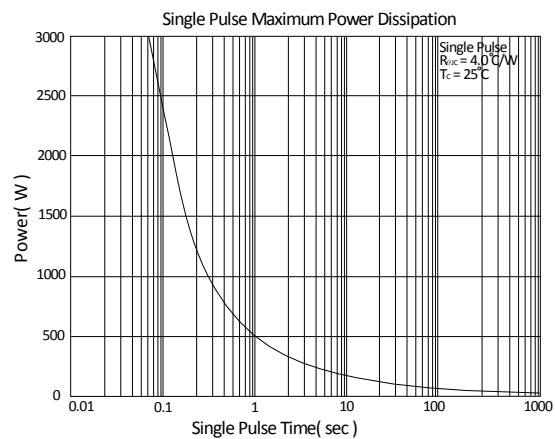
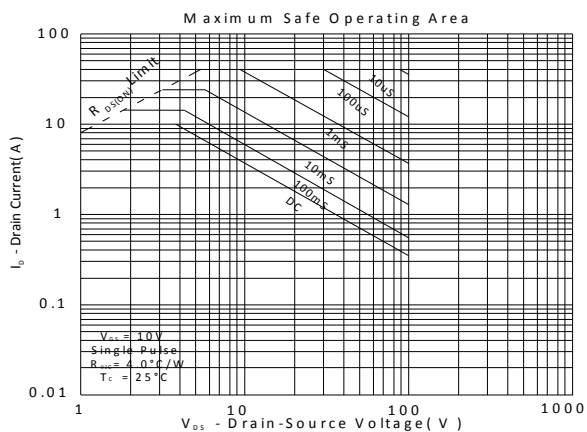
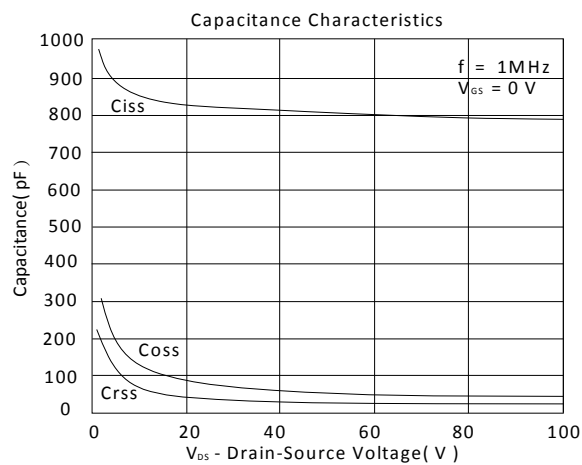
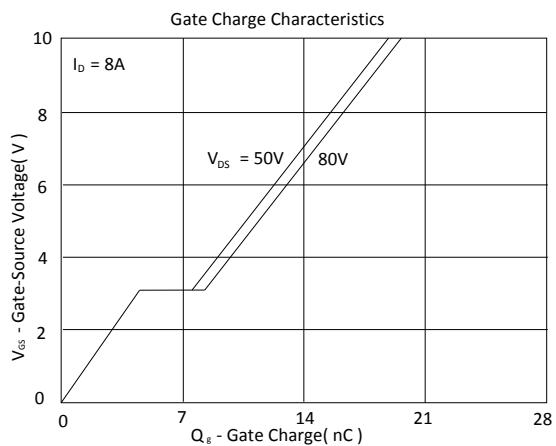
Ordering & Marking Information:

Device Name: EMBA2N10A for DPAK (TO-252)

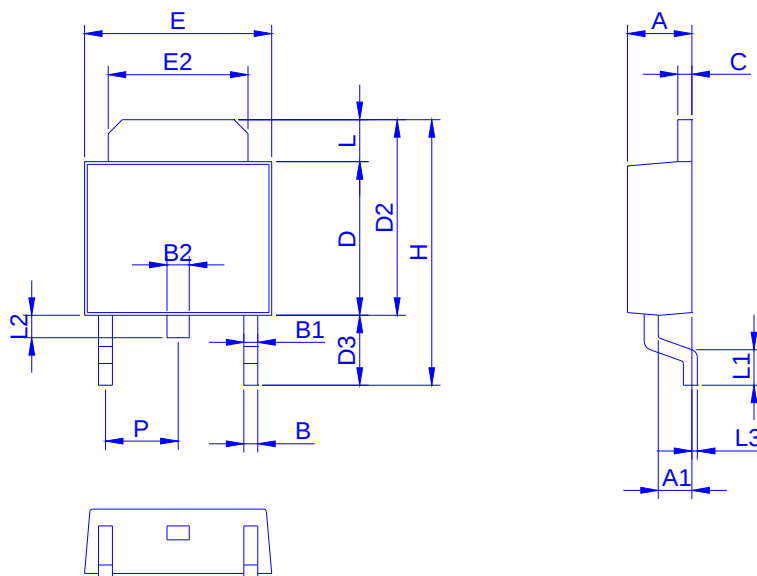


TYPICAL CHARACTERISTICS





Outline Drawing



Dimension in mm

Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50

Footprint

